

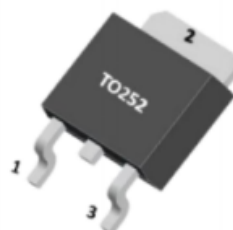
7N65

N-CHANNEL POWER MOSFET

7A, 650V N-CHANNEL POWER MOSFET

DESCRIPTION

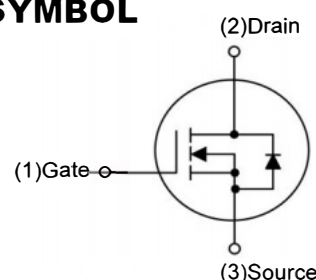
The 7N65 is a high voltage power MOSFET combines advanced planar MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications of switching power supplies and adaptors.



FEATURES

- * $R_{DS(ON)} \leq 1.52 \Omega$ @ $V_{GS}=10V$, $I_D=3A$
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness

SYMBOL



ABSOLUTE MAXIMUM RATINGS($T_A=25^\circ C$, unless otherwise specified.)

SYMBOL	PARAMETER		VALUE	UNIT
V_{DS}	Drain-Source Voltage		650	V
V_{GS}	Gate Source Voltage		± 30	V
I_D	Continuous Drain Current		7	A
I_{DM}	Drain Current Pulsed (Note 2)		14	A
EAS	Avalanche Energy, Single Pulsed (Note 3)		150	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 4)		3.2	V/ns
P_D	Power Dissipation	TO-220F	30	W
		TO-252	50	
T_J	Junction Temperature		150	$^\circ C$
T_{STG}	Storage Temperature		-55 to 150	$^\circ C$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating Pulse width limited by maximum junction temperature.

3. $L = 19.5mH$, $I_{AS} = 4A$, $V_{DD} = 50V$, $R_G = 25 \Omega$, Starting $T_J = 25^\circ C$

4. $I_{SD} \leq 7.0A$, $di/dt \leq 200A/\mu s$, $V_{DD} \leq BV_{DS}$, Starting $T_J = 25^\circ C$



7N65

N-CHANNEL POWER MOSFET

THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220F	θ_{JA}	62.5	$^{\circ}\text{C/W}$
	TO-252		100	
Junction to Case	TO-220F	θ_{JC}	3.4	$^{\circ}\text{C/W}$
	TO-252 (Note)		2.5	

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

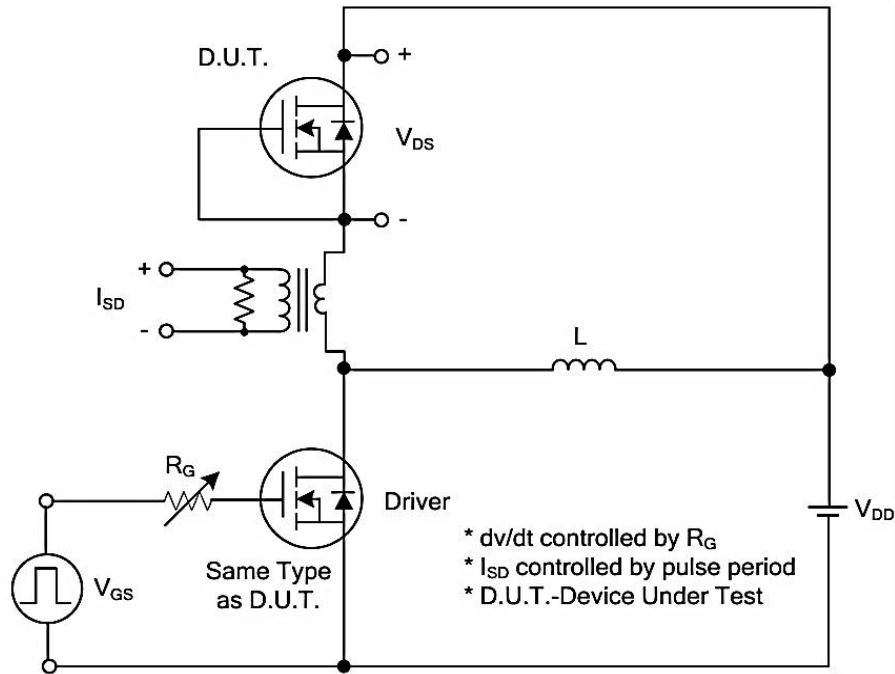
ELECTRICAL CHARACTERISTICS (TA=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	650			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =650V, V _{GS} =0V			1	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =3.0A		1.25	1.52	Ω
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250μA	2.0		4.0	V
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz		750		pF
Output Capacitance	C _{OSS}			65		
Reverse Transfer Capacitance	C _{RSS}			5		
SWITCHING PARAMETERS						
Total gate charge(Note 1)	Q _g	V _{DS} =520V,V _{GS} =10V I _D =7A, I _{GM} =1mA (Note 1, 2)		25		nC
Gate-source charge	Q _{gs}			6.5		
Gate-drain charge	Q _{gd}			5.5		
Turn-On Delay Time(Note 1)	t _{D(on)}	V _{DD} =100V,V _{GS} =10V I _D =7A,R _G =25Ω (Note 1, 2)		10		nS
Turn-On Rise time	t _r			19		
Turn-Off Delay Time	t _{D(off)}			68		
Turn-Off Fall time	t _f			32		
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Maximum Continuous Drain-Source Diode Forward Current	I _S				7	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				14	A
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} = 0 V, I _{SD} =7A			1.4	V
Reverse Recovery Time	t _{rr}	V _{GS} = 0 V, I _{SD} =7A,		325		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 100 A/μs		7.5		μC

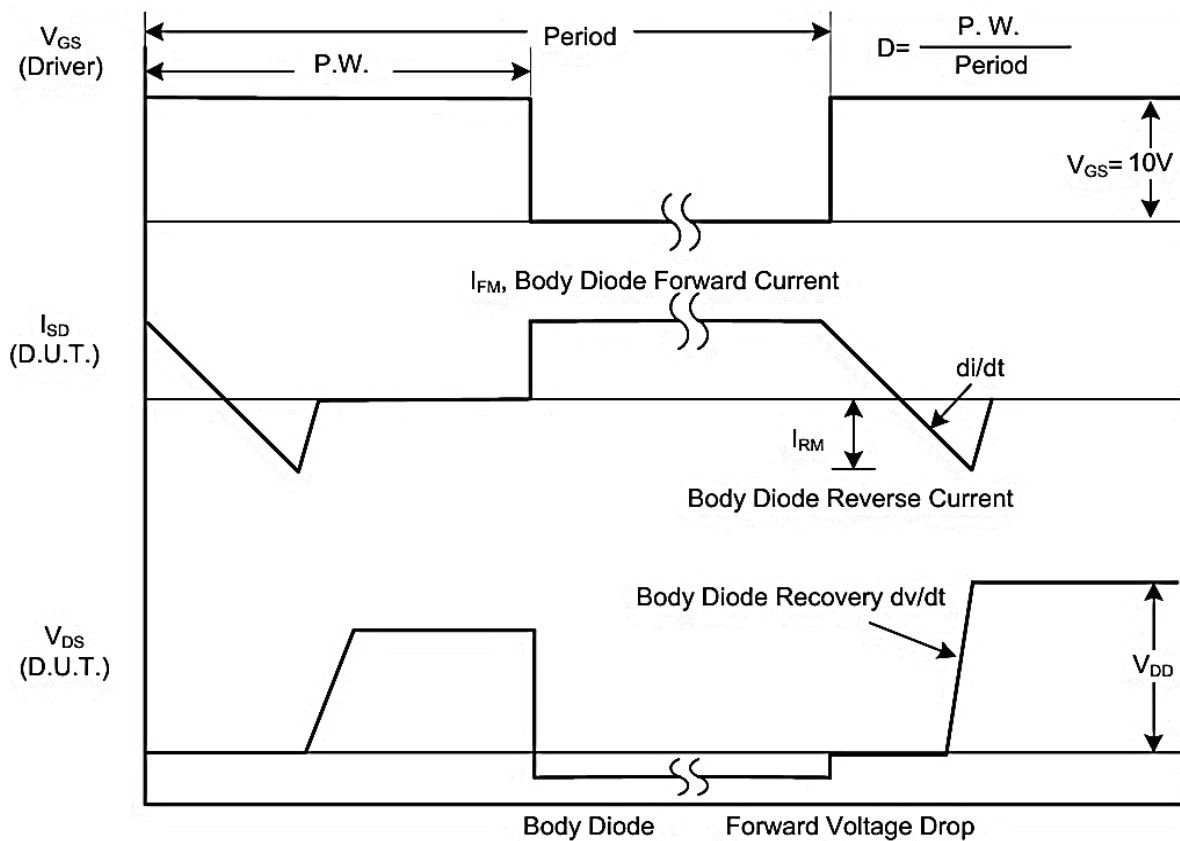
Note:

1. Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$;
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS



Peak Diode Recovery dv/dt Test Circuit

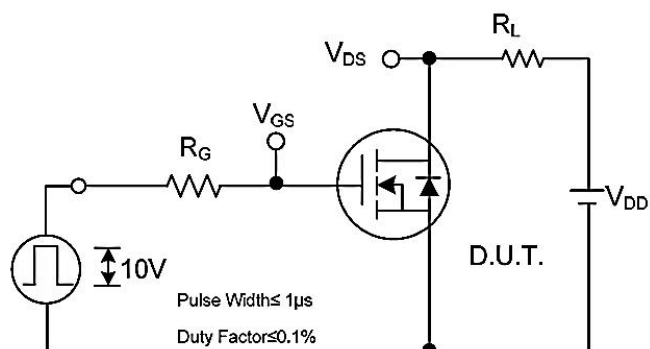


Peak Diode Recovery dv/dt Waveforms

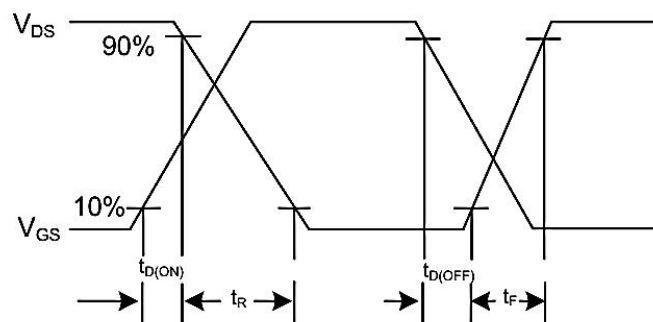
7N65

N-CHANNEL POWER MOSFET

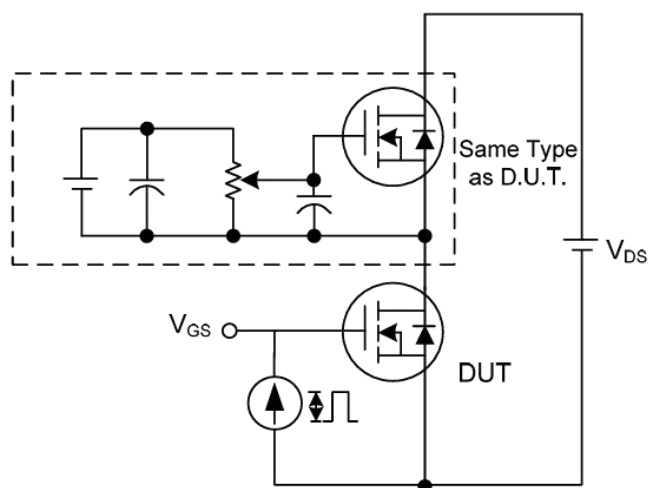
■ TEST CIRCUITS AND WAVEFORMS(Con.t)



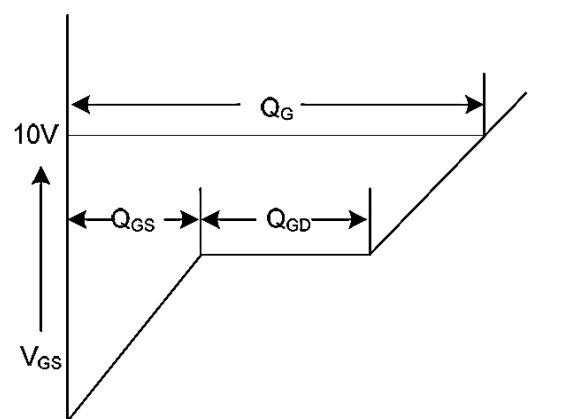
Switching Test Circuit



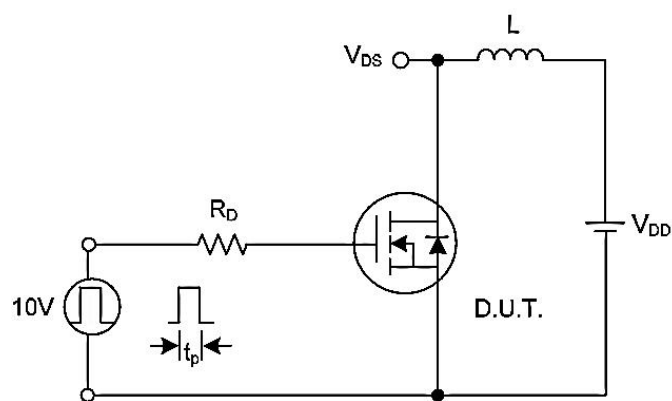
Switching Waveforms



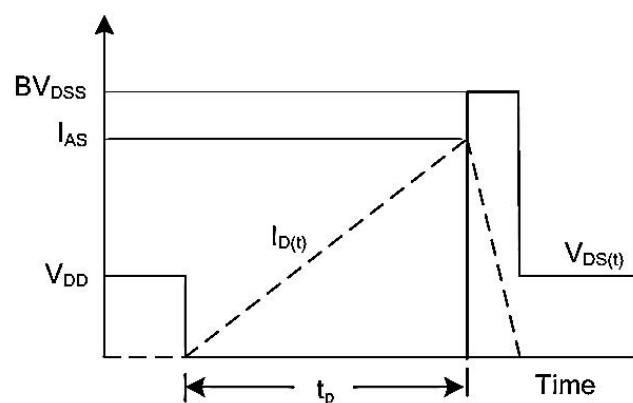
Gate Charge Test Circuit



Charge
Gate Charge Waveform



Unclamped Inductive Switching Test Circuit

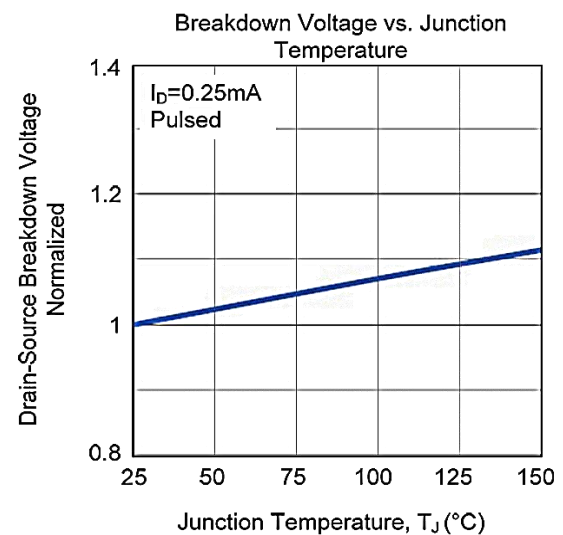
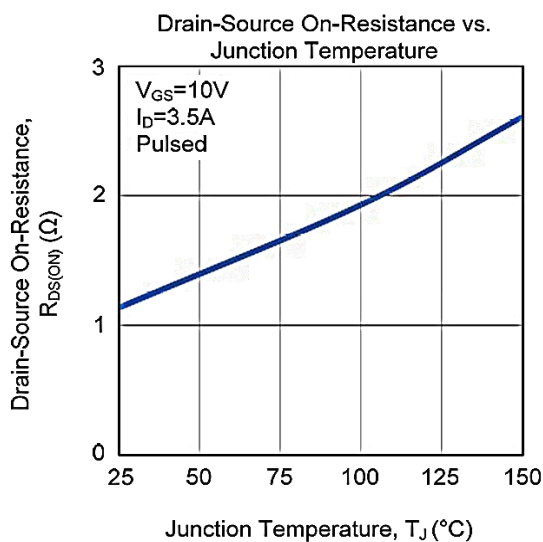
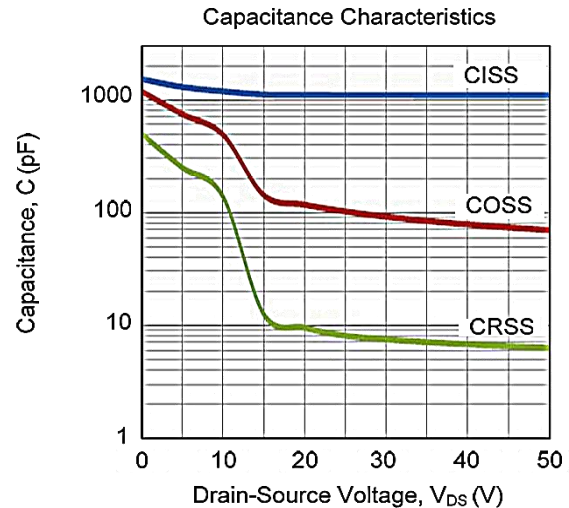
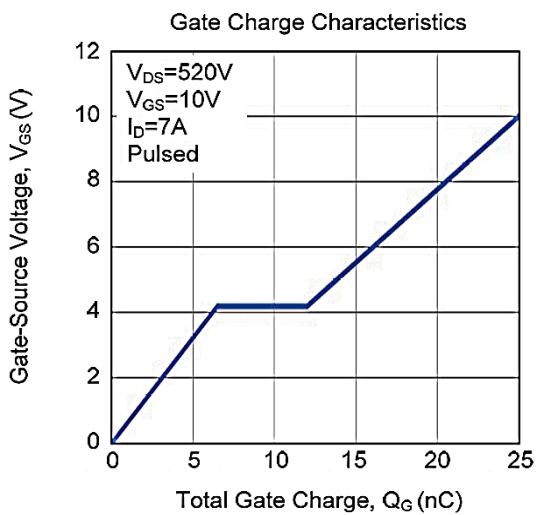
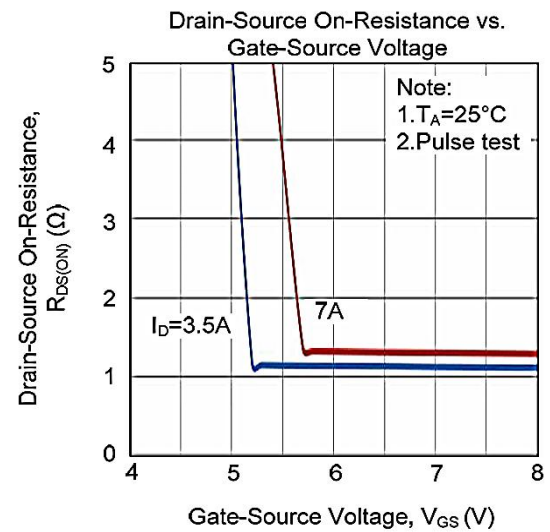
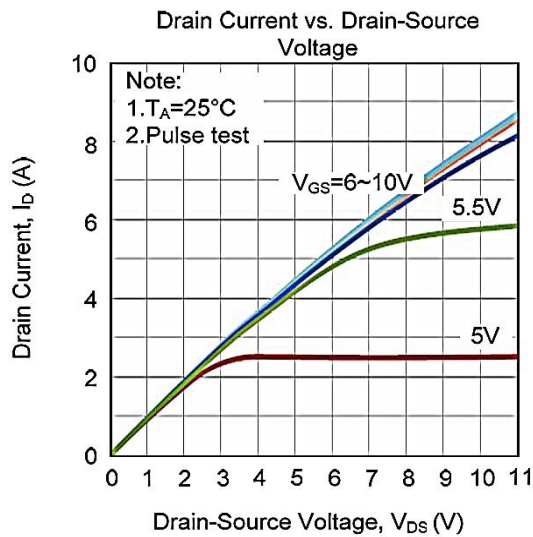


Unclamped Inductive Switching Waveforms

7N65

N-CHANNEL POWER MOSFET

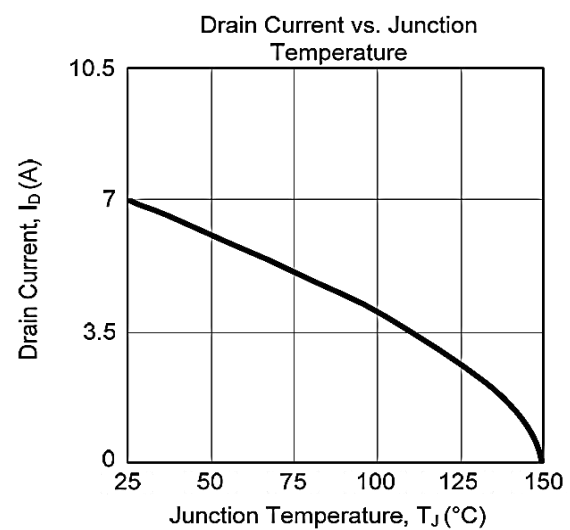
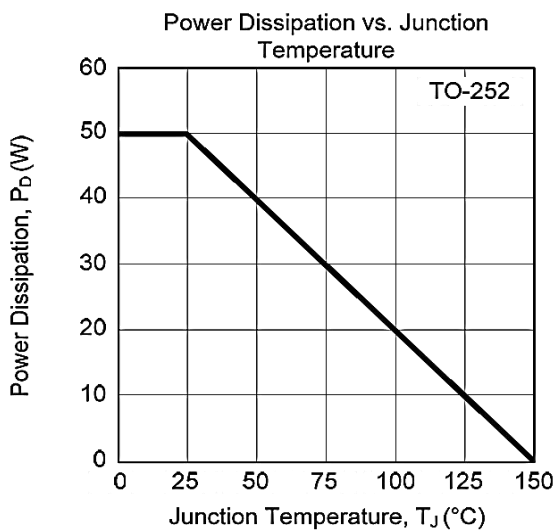
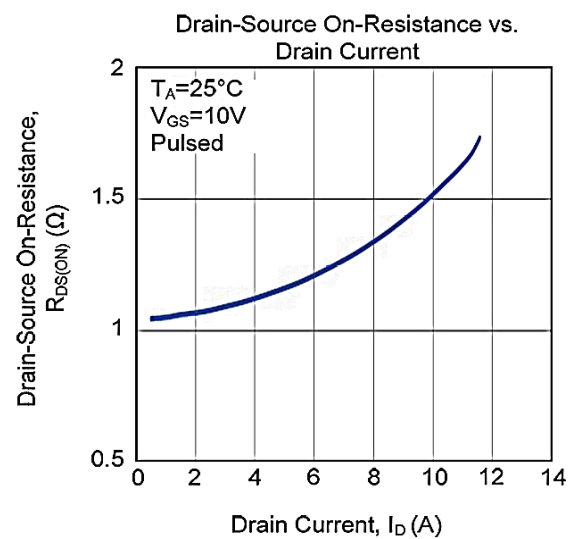
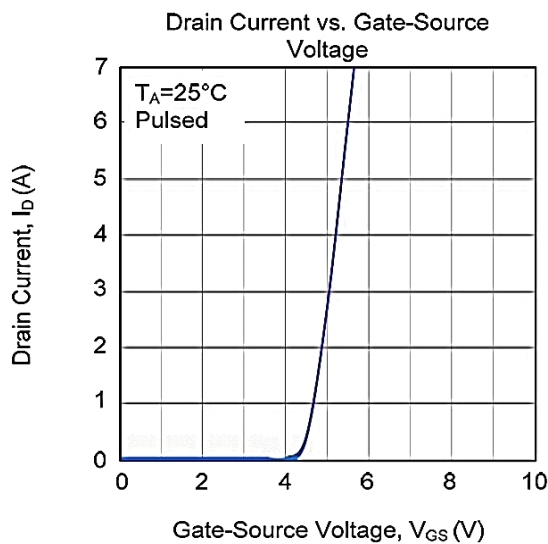
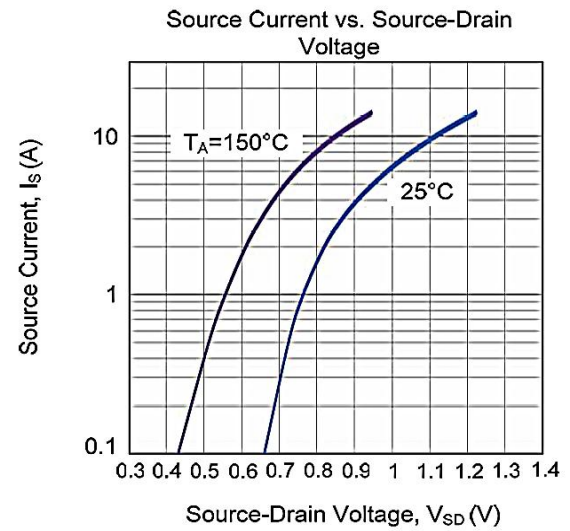
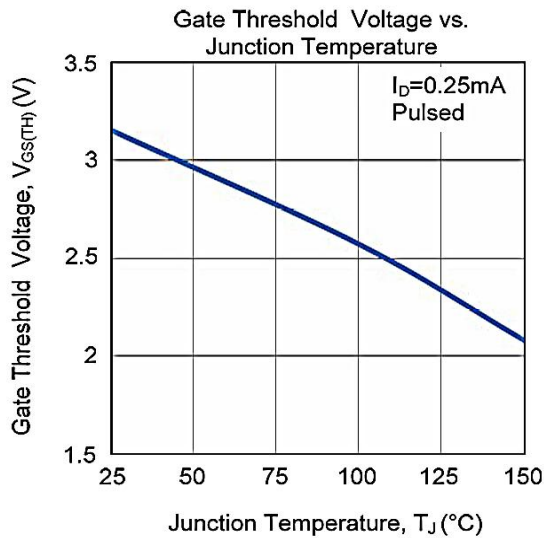
TYPICAL CHARACTERISTICS(1)



7N65

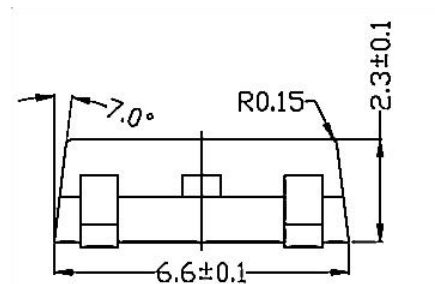
N-CHANNEL POWER MOSFET

TYPICAL CHARACTERISTICS(Con.t)





N-CHANNEL POWER MOSFET



Package version	Reel dimensions $\Phi \times H$ (mm)	Per Reel (pcs)	Reels per box	Inner box dimensions $L \times W \times H$ (mm)	Outer box (pcs)	Outer box dimensions $L \times W \times H$ (mm)
T0-252	$\Phi 330 \times 20$	2500	2	360*340*50	25000	375*375*280